

RGPR10BM40FH

430V 20A Ignition IGBT

BV _{CES}	430±30V
I _C	20A
V _{CE(sat) (Typ.)}	1.6V
E _{AS}	250mJ

Features

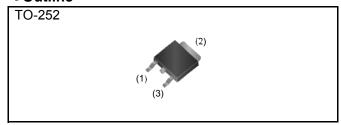
- 1) Low Collector Emitter Saturation Voltage
- 2) High Self-Clamped Inductive Switching Energy
- 3) Built in Gate-Emitter Protection Diode
- 4) Built in Gate-Emitter Resistance
- 5) Qualified to AEC-Q101
- 6) Pb free Lead Plating; RoHS Compliant

Applications

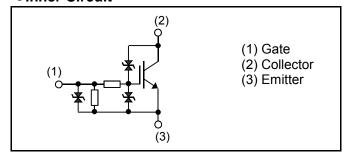
Ignition Coil Driver Circuits

Solenoid Driver Circuits

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Taping
	Reel Size (mm)	330
Typo	Tape Width (mm)	16
Туре	Basic Ordering Unit (pcs)	2,500
	Packing Code	TL
	Marking	RGPR10BM40

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	460	V
Emitter-Collector Voltage (V _{GE} = 0)	/)	V _{EC}	25	V
Gate - Emitter Voltage	V_{GE}	±10	V	
Collector Current	I _C	20	А	
Avalanche Energy (Single Pulse)	T _j = 25°C	E _{AS}	250	mJ
	T _j = 150°C	E _{AS} ^{*2}	150	mJ
Power Dissipation	P _D	107	W	
Operating Junction Temperature	T _j	-40 to +175	°C	
Storage Temperature	T _{stg}	-55 to +175	°C	

●Thermal Resistance

Parameter	Symbol	Values			Unit
- Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance Junction - Case	$R_{\theta(j-c)}$	-	1	1.40	°C/W

● Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Darameter	Cymbol	Conditions	Values			l leit
Parameter	Symbol	Conditions		Тур.	Max.	Unit
		$I_C = 2mA$, $V_{GE} = 0V$				
Collector - Emitter Breakdown Voltage	BV _{CES}	T _j = 25°C	400	430	460	V
		$T_j = -40 \text{ to } 175^{\circ}\text{C}^{*2}$	395	-	465	V
Emitter - Collector Breakdown Voltage	BV _{EC}	$I_{C} = -10 \text{mA}, V_{GE} = 0 \text{V}$	25	35	ı	٧
Gate - Emitter Breakdown Voltage	BV _{GES}	$I_G = \pm 5$ mA, $V_{CE} = 0$ V	±12	-	±17	V
		V _{CE} = 300V, V _{GE} = 0V				
Collector Cut - off Current	I _{CES}	T _j = 25°C	-	-	7	μA
		$T_j = 150^{\circ}C^{*2}$	-	-	100	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 10V, V_{CE} = 0V$	±0.4	±0.6	±1.2	mA
		V _{CE} = 5V, I _C = 10mA				
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	T _j = 25°C	1.3	1.7	2.1	V
· o.u.go		T _j = 150°C	-	1.3	-	V
		I _C = 10A, V _{GE} = 5V				
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	T _j = 25°C	-	1.60	2.00	V
5		T _j = 150°C	-	1.80	-	V
		$I_C = 4A, V_{GE} = 4.5V$				
Collector - Emitter Saturation Voltage	V _{CE(sat)}	T _j = 25°C	-	1.17	1.50	V
		T _j = 150°C	-	1.13	-	V

●Electrical Characteristics (at T_j = 25°C unless otherwise specified)

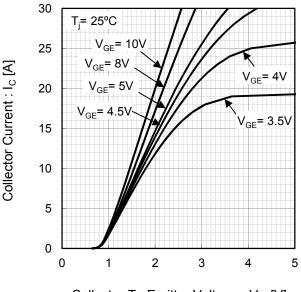
Parameter Symb	Symbol	Conditions	Values			Unit
	Symbol	Conditions	Min.	Тур.	Max.	Uniit
Collector - Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	I_{C} = 10A, V_{GE} = 4V T_{j} = 25°C T_{j} = 150°C	-	1.70 1.90	2.10	V V
Input Capacitance	C _{ies}	V _{CE} = 10V	-	1000	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	175	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	55	-	
Total Gate Charge	Q_{g}	$V_{CE} = 15V, I_{C} = 10A,$ $V_{GE} = 5V$	-	14	-	nC
Turn - on Delay Time*1,*2	t _{d(on)}		0.09	0.17	0.50	
Rise Time*1,*2	t _r	$I_C = 8A, V_{CC} = 300V,$ $V_{GE} = 5V, R_G = 100\Omega,$	0.10	0.18	0.50	μs
Turn - off Delay Time*1,*2	$t_{d(off)}$	$L=5mH, T_j=25^{\circ}C$	0.8	1.3	4.0	
Fall Time*1,*2	t _f		1.4	2.4	6.0	
Turn - on Delay Time*1	$t_{d(on)}$		1	0.16	ı	
Rise Time*1	t _r	$I_C = 8A, V_{CC} = 300V,$ $V_{GE} = 5V, R_G = 100\Omega,$	1	0.23	ı	Пе
Turn - off Delay Time*1	$t_{\text{d(off)}}$	L=5mH, T_j =150°C	1	1.5	ı	μs
Fall Time ^{*1}	t_f		ı	3.9	ı	
Avalancha Energy (Single Dulce)	E _{AS}	$L = 5\text{mH}, V_{GE} = 5V,$ $V_{CC} = 30V, R_G = 1k\Omega,$				
Avalanche Energy (Single Pulse)		T _j = 25°C	250	-	-	mJ
		$T_j = 150^{\circ}C^{*2}$	150	-	1	mJ
Gate Series Resistance	R_{G}		70	100	130	Ω
Gate - Emitter Resistance	R_GE		8	16	24	kΩ

^{*1)} Assurance items according to our measurement definition (Fig.16)

^{*2)} Design assurance items

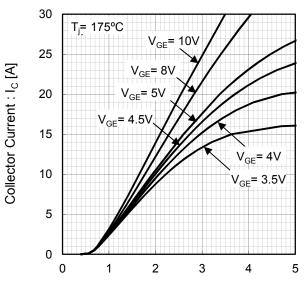
Electrical Characteristic Curves

Fig.1 Typical Output Characteristics



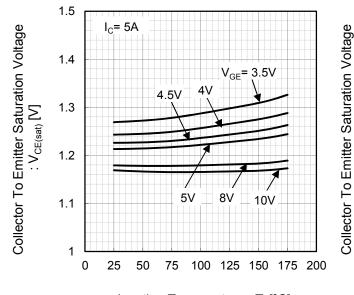
Collector To Emitter Voltage : $V_{CE}[V]$

Fig.2 Typical Output Characteristics



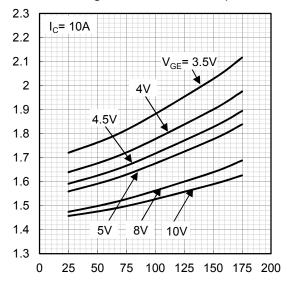
Collector To Emitter Voltage : V_{CE}[V]

Fig.3 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.4 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

 $: V_{CE(sat)}[M]$

Electrical Characteristic Curves

Fig.5 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

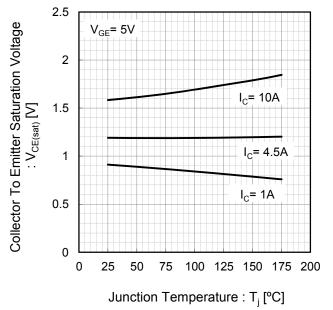


Fig.6 Typical Transfer Characteristics

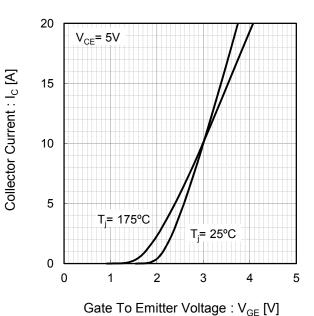
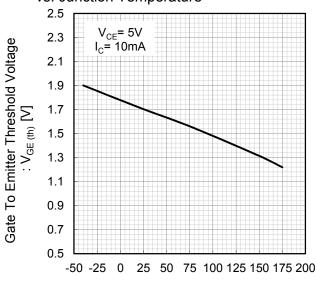


Fig.7 Typical Gate To Emitter Threshold Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

vs. Junction Temperature 10000 Leakage Current : I_{CES}/I_{EC} [μΑ] 1000 V_{EC}= 25V 100 10 1 V_{CES}= 300V 0.1 0.01 25 50 75 100 125 150 175 200 -50 -25 0

Fig.8 Typical Leakage Current

Junction Temperature : T_i [°C]

Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Breakdown Voltage vs. Junction Temperature

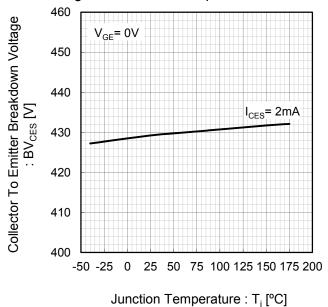


Fig.10 Typical Self Clamped Inductive Switching Current vs. Inductance

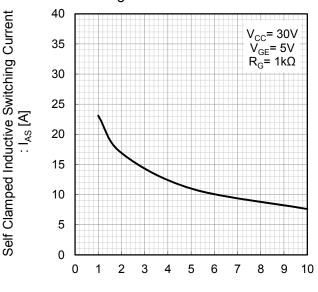


Fig.11 Typical Gate Charge

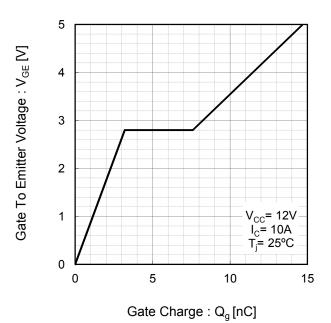
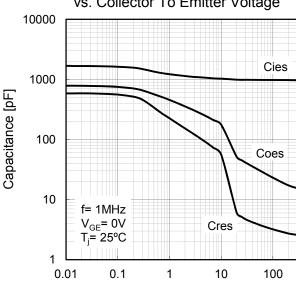


Fig.12 Typical Capacitance vs. Collector To Emitter Voltage

Inductance: L[mH]



Collector To Emitter Voltage : V_{CE}[V]

0.1 L 0

25

50

75

•Electrical Characteristic Curves

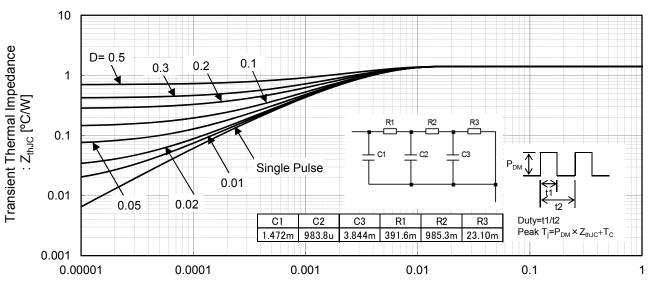
Fig.13 Typical Switching Time vs. Junction Temperature

10 $V_{cc} = 30V, I_{c} = 8A, V_{GE} = 5V, L = 5mH, R_{g} = 100\Omega$ 1 $t_{d(off)}$

Junction Temperature : T_i [°C]

100 125 150 175 200

Fig.14 Transient Thermal Impedance



Pulse Width: t1[s]

•Inductive Load Switching Circuit and Waveform

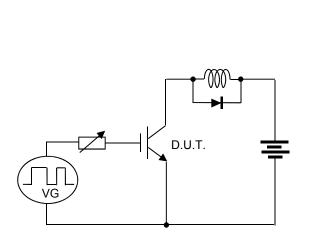


Fig.15 Inductive Load Switching Circuit

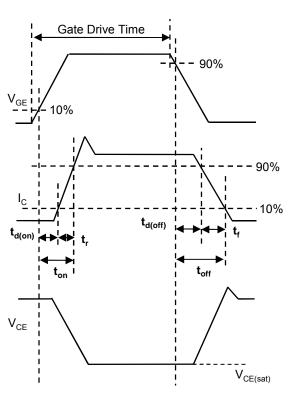
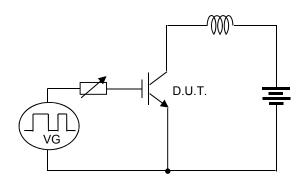


Fig.16 Inductive Load Switching Waveform

● Self Clamped Inductive Switching Circuit and Waveform



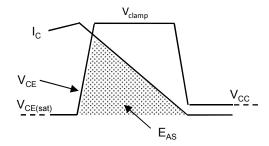


Fig.17 Self Clamped Inductive Switching Circuit

Fig.18 Self Clamped Inductive Switching Waveform

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RGPR10BM40FH - Web Page

Distribution Inventory

Part Number	RGPR10BM40FH
Package	TO-252
Unit Quantity	2500
Minimum Package Quantity	2500
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes